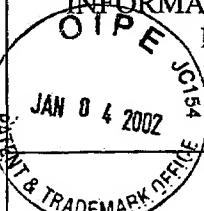


Form PTO-1449

INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

(Use several sheets if necessary)



Docket Number 299002048410 Application Number 09/904,162

Applicant

Y. Tsuda, et al.

Filing Date July 11, 2001

Group Art Unit 2813

Mailing Date November 24 2001

## U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate
		/	/	/	/	/	

## FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO
			/	/	/	/	

## OTHER DOCUMENTS

(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
Duplicate	1.	Sunakawa et al. (1997). "Thick GaN crystal growth with low defect density by hydride-vapor phase epitaxy" Ext. Abstract. (The 58th Autumn Meeting) J. Soc. of Appl. Phys. No. 1 266 2p-Q-15
M	2.	Tanaka et al. (1997). "Reduced dislocation densities in selectivity-grown nitride materials" Ext. Abstract. (The 58th Autumn Meeting) J. Soc. of Appl. Phys. No. 1 265 2p-Q-14.

Ref#1 on Form 892 paper # 3

TC 2000 MAIL ROOM  
RECEIVED  
JAN 11 2002  
U.S. PATENT & TRADEMARK OFFICE

EXAMINER:	<i>R. OSA</i>	DATE CONSIDERED:	<i>1/20/02</i>
-----------	---------------	------------------	----------------

EXAMINER: Initial if citation considered, whether or not the citation conforms with MPEP 609. Draw a line through the citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.